Discrete POWER & Signal **Technologies** 

# 2N5306

FAIRCHILD SEMICONDUCTOR TM

2N5306



# **NPN Darlington Transistor**

This device is designed for applications requiring extremely high current gain at currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>CBO</sub>	Collector-Base Voltage	25	V
$V_{\text{EBO}}$	Emitter-Base Voltage 12		V
Ic	Collector Current - Continuous 1.2 A		A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted			
Symbol	Characteristic	Max	Units
		2N5306	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W

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# NPN Darlington Trar (0

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		Test Conditions	Min	Max	Units
OFF CHAR	RACTERISTICS				
/ <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	25		V
/ <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 0.1 \ \mu {\rm A}, \ I_{\rm E} = 0$	25		V
/ <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{E} = 0.1 \mu A, I_{C} = 0$	12		V
СВО	Collector Cutoff Current	$V_{CB} = 25 \text{ V}, \text{ I}_{E} = 0$		0.1	μΑ
		$V_{CB} = 25 \text{ V}, I_E = 0, T_A = 100 \text{ °C}$ $V_{EB} = 12 \text{ V}, I_C = 0$		20	μA
EBO	Emitter Cutoff Current	$V_{EB} = 12 V, I_{C} = 0$		0.1	μA
	ACTERISTICS*				
	DC Current Gain		7 000	70.000	r
η <sub>FE</sub>	De current Gam	$V_{CE} = 5.0 \text{ V}, I_C = 2.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 100 \text{ mA}$	7,000 20,000	70,000	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 200 \text{ mA}, I_{\rm B} = 0.2 \text{ mA}$	,	1.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_{\rm C} = 200 \text{ mA}, I_{\rm B} = 0.2 \text{ mA}$		1.6	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{\rm C}$ = 200 mA, $V_{\rm CE}$ = 5.0 V		1.5	V
			-		
SMALL SIG	GNAL CHARACTERISTICS				
C <sub>cb</sub>	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		10	pF
λfe	Small-Signal Current Gain	$I_{\rm C} = 2.0 \text{ mA}, V_{\rm CE} = 5.0 \text{ V},$			
		f = 1.0 kHz I <sub>c</sub> =2.0 mA, V <sub>CE</sub> = 5.0 V,	7,000		
		f = 10  MHz	6.0		
*Dulas Testi F	Pulse Width ≤ 300 u.s. Duty Cvcle ≤ 2.0%				
Fuise Test. F	Fulse width $\leq$ 500 µs, Duty Cycle $\leq$ 2.0%				



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